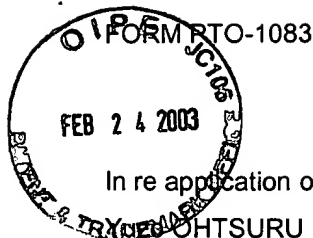


2612



PATENT
5586D-6845 (81784.0179)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

RYOBUCHTSURU

Serial No: 09/135,180

Filed: August 17, 1998

For: SOLID-STATE IMAGE PICKUP DEVICE FOR
PRODUCING THINNED IMAGE

Art Unit: 2612

Examiner: Luong T. Nguyen

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to:

Commissioner for Patents
Washington D.C. 20231, on

February 19, 2003

Date of Deposit

John P. Scherlach, Reg. No. 23,009

Name

Signature

02/19/03

Date

Box Non-Fee Amendment
Commissioner for Patents
Washington, D.C. 20231

FEB 26 2003

Technology Center 2600

Dear Sir:

Transmitted herewith is an amendment in the above-identified application.

- ☐ Small entity status of this application under 37 C.F.R. 1.9 and 1.27 has been established by a verified statement previously submitted.
- ☐ A verified statement to establish small entity status under 37 C.F.R. 1.9 and 1.27 is enclosed.
- ☐ A Notice Of Change Of Attorney's Address and Associate Power Of Attorney is enclosed.
- ☒ No additional fee is required.

The fee has been calculated as shown below:

YOU HAVE BEEN CALCULATED AS SHOWN BELOW:								
	(Col. 1) CLAIMS REMAINING AFTER AMENDMENT		(Col. 2) HIGHEST NUMBER PREVIOUSLY PAID FOR	(Col. 3) PRESENT EXTRA*	LG/SM \$ ENTITY FEE		ADD'L FEE DUE	
TOTAL CLAIMS FEE	20	-20	20 **	0	LG=\$18 SM=\$9	\$18	\$ 0	
INDEPENDENT CLAIMS FEE	5	-3	5 ***	0	LG=\$84 SM=\$42	\$84	\$ 0	
FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIMS					LARGE ENTITY FEE = \$280 SMALL ENTITY FEE = \$140		\$	
TOTAL							\$ 0	

* If the entry in Col. 1 is less than the entry in Col. 2, write "0" in Col. 3.

** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, write "20" in this space.

*** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space. The "Highest Number Previously Paid For" (Total or Independent) is the highest number found from the equivalent box on Col. 1 of a prior amendment or the number of claims originally filed.

- ☐ A check in the amount of \$-0- to cover the additional claims fee is enclosed. A copy of this sheet is enclosed.
- ☐ A check in the amount of \$-0- to cover the extension fee is enclosed. A copy of this sheet is enclosed.
- ☒ The Commissioner is hereby authorized to charge any deficiencies of fees associated with this communication or credit any overpayment to Deposit Account No. 50-1314. A copy of this sheet is enclosed.
- ☒ Any filing fees under 37 C.F.R. 1.16 for the presentation of extra claims
- ☒ Any patent application processing fees under 37 C.F.R. 1.17

Respectfully submitted,
HOGAN & HARTSON L.L.P.

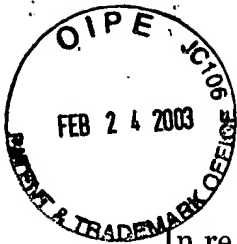
By:

John P. Scherlach

Registration No. 23,009

Attorney for Applicant(s)

Date: February 19, 2003
Biltmore Tower
500 South Grand Avenue, Suite 1900
Telephone: 213 337-6700
Facsimile: 213 337-6701



PATENT
5586D-6845 (81784.0179)

Handwritten initials and date: 2/26/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Yuzo OHTSURU

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John P. Scherlacher, Reg. No. 23,009

Name

John P. Scherlacher 02/19/03

Signature

Date

AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, D.C. 20231

RECEIVED

FEB 26 2003

Technology Center 2600

Dear Sir:

In response to the Office Action dated November 20, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION:

On pages 12 and 13, rewrite the paragraph beginning at line 11 of page 12 and ending at line 13 of page 13, as follows:

A P-type diffusion region 12 is formed on one principal face of an N-type semiconductor substrate 11, and a plurality of channel regions extending in one direction (horizontal direction of Fig. 4) are formed parallel with one another in the diffusion region 12. Each channel region forms a transfer route of information charges, and has an N-type embedded layer 13 in the vicinity of its surface, which forms an embedded channel structure. Furthermore, the semiconductor substrate 11 serves as an overflow drain for absorbing the information charges leaking from the channel regions, to which predetermined fixed potentials are applied in accumulating, transfer and discharge periods of the information charges, respectively. A plurality of transfer electrodes 15 extend in a direction intersecting the channel regions and arranged parallel with one another via an insulating film